

Silicon Carbide (SiC) Schottky Diode – EliteSiC, 20 A, 650 V, D2, TO-220-2L

FFSP2065B-F085

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

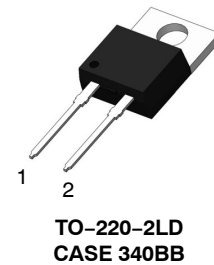
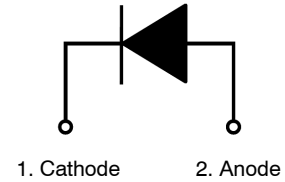
Features

- Max Junction Temperature 175°C
- Avalanche Rated 94 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

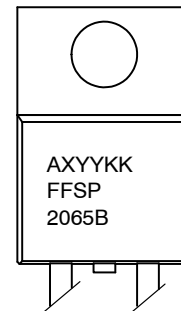
Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

ELECTRICAL CONNECTION



MARKING DIAGRAM



| | |
|-----------|---------------------------|
| A | = Assembly Plant Code |
| XY | = Date Code (Year & Week) |
| YK | = Lot Traceability Code |
| FFSP2065B | = Specific Device Code |

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

FFSP2065B–F085

ABSOLUTE MAXIMUM RATINGS

($T_C = 25^\circ\text{C}$, Unless otherwise specified)

| Symbol | Parameter | FFSP2065B–F085 | Unit |
|----------------|--|--|------------------|
| V_{RRM} | Peak Repetitive Reverse Voltage | 650 | V |
| E_{AS} | Single Pulse Avalanche Energy (Note 1) | 94 | mJ |
| I_F | Continuous Rectified Forward Current @ $T_C < 141^\circ\text{C}$ | 20 | A |
| | Continuous Rectified Forward Current @ $T_C < 135^\circ\text{C}$ | 22.5 | |
| $I_{F, Max}$ | Non–Repetitive Peak Forward Surge Current | $T_C = 25^\circ\text{C}$, 10 μs | 882 |
| | | $T_C = 150^\circ\text{C}$, 10 μs | 798 |
| $I_{F, SM}$ | Non–Repetitive Forward Surge Current | Half–Sine Pulse, $t_p = 8.3 \text{ ms}$ | 84 |
| P_{tot} | Power Dissipation | $T_C = 25^\circ\text{C}$ | 150 |
| | | $T_C = 150^\circ\text{C}$ | 25 |
| T_J, T_{STG} | Operating and Storage Temperature Range | –55 to +175 | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 94 mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 0.5 \text{ mH}$, $I_{AS} = 19.4 \text{ A}$, $V = 50 \text{ V}$.

THERMAL CHARACTERISTICS

| Symbol | Parameter | Ratings | Unit |
|-----------------|--|---------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max. | 1.0 | $^\circ\text{C}/\text{W}$ |

ELECTRICAL CHARACTERISTICS $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------|-------------------------|---|------|------|------|---------------|
| V_F | Forward Voltage | $I_F = 20 \text{ A}$, $T_C = 25^\circ\text{C}$ | – | 1.38 | 1.7 | V |
| | | $I_F = 20 \text{ A}$, $T_C = 125^\circ\text{C}$ | – | 1.6 | 2.0 | |
| | | $I_F = 20 \text{ A}$, $T_C = 175^\circ\text{C}$ | – | 1.72 | 2.4 | |
| I_R | Reverse Current | $V_R = 650 \text{ V}$, $T_C = 25^\circ\text{C}$ | – | 0.5 | 40 | μA |
| | | $V_R = 650 \text{ V}$, $T_C = 125^\circ\text{C}$ | – | 1 | 80 | |
| | | $V_R = 650 \text{ V}$, $T_C = 175^\circ\text{C}$ | – | 2 | 160 | |
| Q_C | Total Capacitive Charge | $V = 400 \text{ V}$ | – | 51 | – | nC |
| C | Total Capacitance | $V_R = 1 \text{ V}$, $f = 100 \text{ kHz}$ | – | 866 | – | pF |
| | | $V_R = 200 \text{ V}$, $f = 100 \text{ kHz}$ | – | 80 | – | |
| | | $V_R = 400 \text{ V}$, $f = 100 \text{ kHz}$ | – | 70 | – | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PACKAGE MARKING AND ORDERING INFORMATION

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|----------------|-----------|------------|----------------|-----------|------------|----------|
| FFSP2065B–F085 | FFSP2065B | TO–220–2LD | Tube | N/A | N/A | 50 Units |

TYPICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED

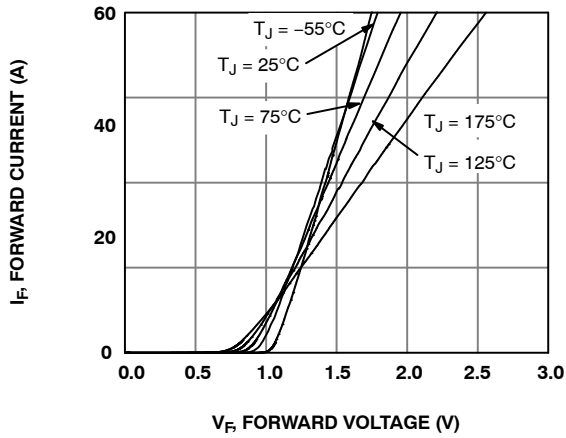


Figure 1. Forward Characteristics

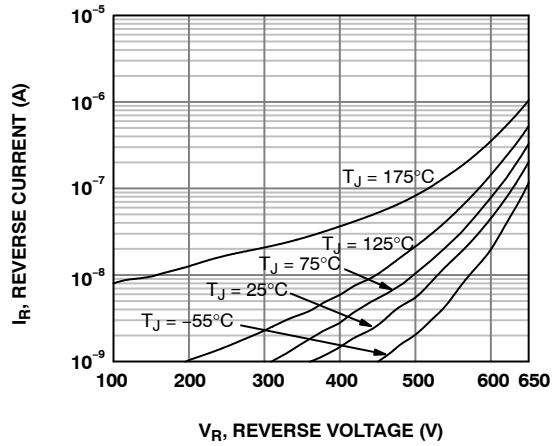


Figure 2. Reverse Characteristics

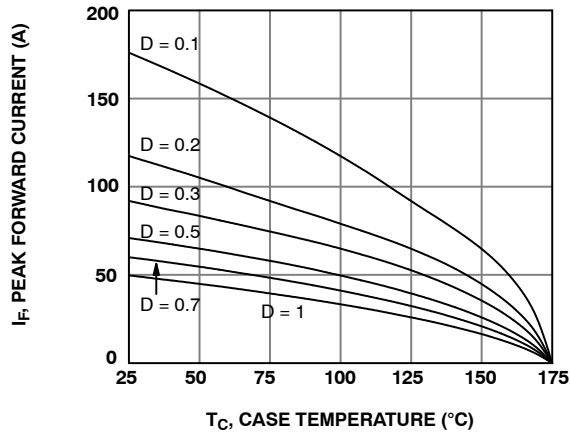


Figure 3. Current Derating

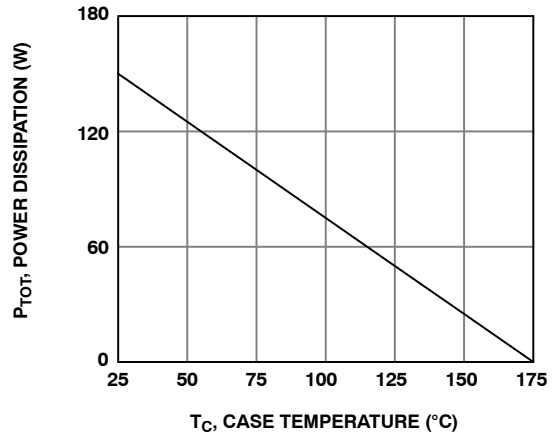


Figure 4. Power Dissipation

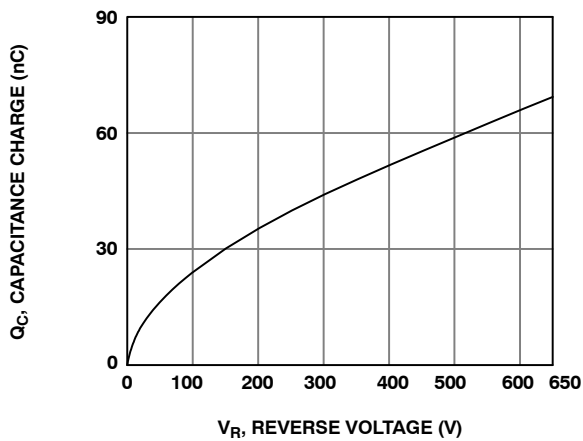


Figure 5. Capacitance Charge vs. Reverse Voltage

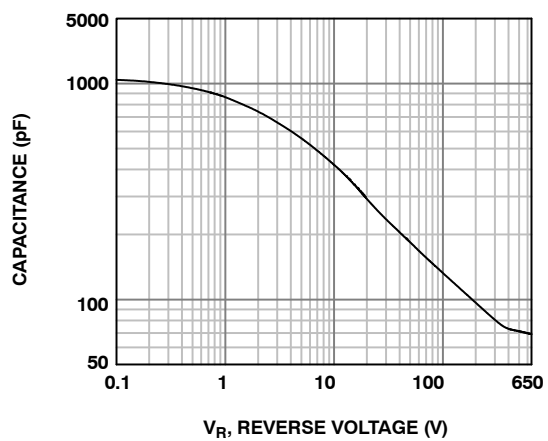


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED (CONTINUED)

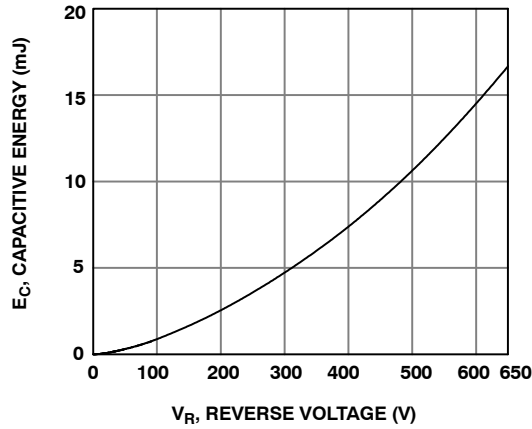


Figure 7. Capacitance Stored Energy

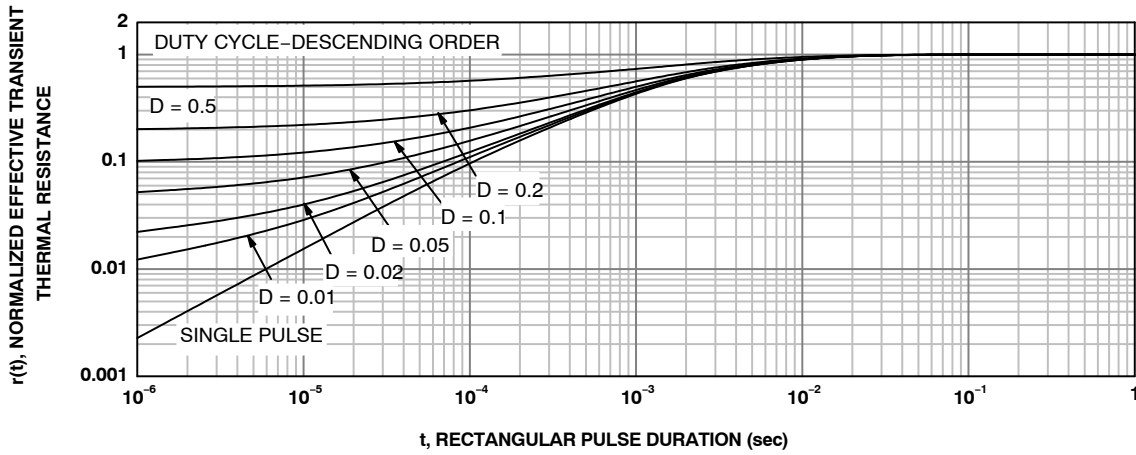


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

$L = 0.5 \text{ mH}$
 $R < 0.1 \Omega$
 $V_{DD} = 50 \text{ V}$
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$
 $Q1 = \text{IGBT (}BV_{CES} > DUT V_{R(AVL)}\text{)}$

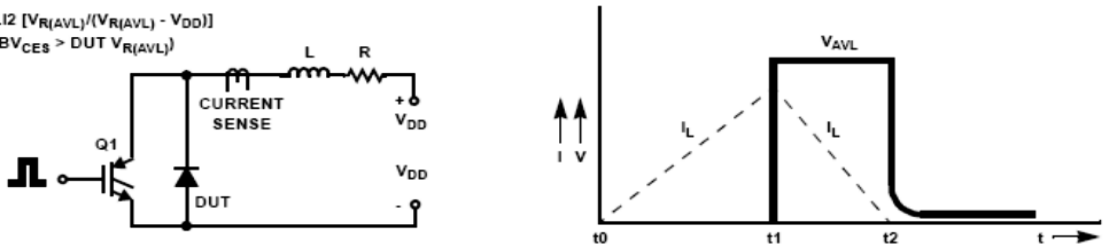


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®



TO-220-2LD
CASE 340BB
ISSUE O

DATE 31 AUG 2016



NOTES:

- A. PACKAGE REFERENCE: JEDEC TO220,ISSUE K, VARIATION AC, DATED APRIL 2002.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

| | | |
|-------------------------|--------------------|--|
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| DESCRIPTION: | TO-220-2LD | PAGE 1 OF 1 |

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